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MOS INTEGRATED CIRCUIT



USB2.0 to IDE Bridge



The μ PD720130 is designed to perform a bridge between USB 2.0 and ATA/ATAPI. The μ PD720130 complies with the Universal Serial Bus Specification Revision 2.0 full-/high-speed signaling and works up to 480 Mbps. The μ PD720130 is integrated CISC processor, ATA/ATAPI controller, endpoint controller (EPC), serial interface engine (SIE), and USB2.0 transceiver into a single chip. The USB2.0 protocol and class specific protocol (bulk only protocol) are handled by USB2.0 transceiver, SIE, and EPC. And the transport layer is performed by V30MZ CISC processor which is in the μ PD720130. The software to control the μ PD720130 is located in an embedded ROM. In the future, the μ PD720130 will be released to support external Flash Memory / EEPROMTM option to update function by firmware.

Detailed function descriptions are provided in the following user's manual. Be sure to read the manual before designing. μ PD720130 User's Manual: S16412E

FEATURES

- Compliant with Universal Serial Bus Specification Revision 2.0 (Data Rate 12/480 Mbps)
- Compliant with ATA/ATAPI-6 (LBA48, PIO Mode 0-4, Multi Word DMA Mode 0-2, Ultra DMA Mode 0-4)
- · USB2.0 high-speed bus powered device capability
- Certified by USB implementers forum and granted with USB 2.0 high-speed Logo (TID: 40320125)
- One USB2.0 high-speed transceiver / receiver with full-speed transceiver / receiver
- USB2.0 High-speed or Full-speed packet protocol sequencer (Serial Interface Engine)
- · Automatic chirp assertion and full-/high-speed mode change
- USB Reset, Suspend and Resume signaling detection
- · Supports power control functionality for IDE device as CD-ROM and HDD
- Supports set feature (TEST_MODE) functionality
- System Clock is generated by 30 MHz X'tal
- 2.5 V and 3.3 V power supply

ORDERING INFORMATION

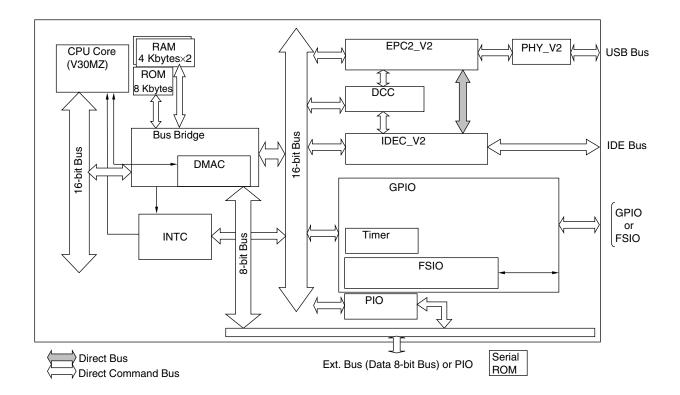
Part Number	Package
μ PD720130GC-9EU	100-pin plastic TQFP (fine pitch) (14 \times 14)
μ PD720130GC-9EU-SIN	100-pin plastic TQFP (fine pitch) (14 \times 14)
μ PD720130GC-9EU-A	100-pin plastic TQFP (fine pitch) (14 \times 14)

★ Remark μPD720130GC-9EU-A is a lead-free product.

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BLOCK DIAGRAM



V30MZ : CISC CPU core

RAM : 8-Kbyte work RAM for firmware ROM : 8-Kbyte ROM for built-in firmware

PHY_V2 : USB2.0 transceiver with serial interface engine

EPC_V2 : Endpoint controller IDEC_V2 : IDE controller

DCC : ATA direct command controller

Bus Bridge : Internal / external bus controller and DMA controller

INTC : Interrupt controller (82C59 like)
GPIO : General purpose 8-bit I/O controller
PIO : Multipurpose 14-bit I/O controller

FSIO : Flexible serial I/O



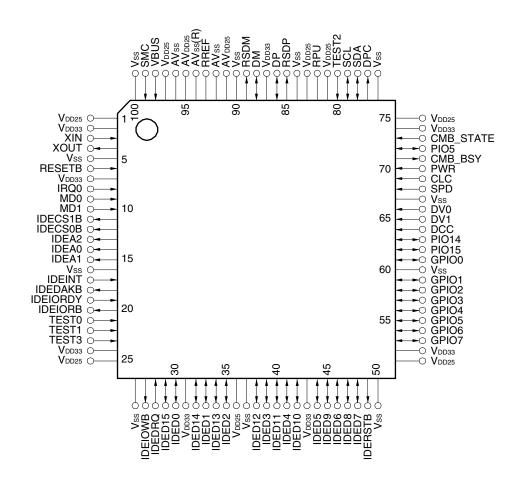
PIN CONFIGURATION (TOP VIEW)

• 100-pin plastic TQFP (fine pitch) (14 × 14)

 μ PD720130GC-9EU

 μ PD720130GC-9EU-SIN

μPD720130GC-9EU-A





PIN LIST

Pin No.	Pin Name						
1	V _{DD25}	26	Vss	51	V _{DD25}	76	Vss
2	V _{DD33}	27	IDEIOWB	52	V _{DD33}	77	DPC
3	XIN	28	IDEDRQ	53	GPIO7	78	SDA
4	XOUT	29	IDED15	54	GPIO6	79	SCL
5	Vss	30	IDED0	55	GPIO5	80	TEST2
6	RESETB	31	V _{DD33}	56	GPIO4	81	V _{DD25}
7	V _{DD33}	32	IDED14	57	GPIO3	82	RPU
8	IRQ0	33	IDED1	58	GPIO2	83	V _{DD25}
9	MD0	34	IDED13	59	GPIO1	84	Vss
10	MD1	35	IDED2	60	Vss	85	RSDP
11	IDECS1B	36	V _{DD25}	61	GPIO0	86	DP
12	IDECS0B	37	Vss	62	PIO15	87	V _{DD33}
13	IDEA2	38	IDED12	63	PIO14	88	DM
14	IDEA0	39	IDED3	64	DCC	89	RSDM
15	IDEA1	40	IDED11	65	DV1	90	Vss
16	Vss	41	IDED4	66	DV0	91	AV _{DD25}
17	IDEINT	42	IDED10	67	Vss	92	AVss
18	IDEDAKB	43	V _{DD33}	68	SPD	93	RREF
19	IDEIORDY	44	IDED5	69	CLC	94	AVss(R)
20	IDEIORB	45	IDED9	70	PWR	95	AV _{DD25}
21	TEST0	46	IDED6	71	CMB_BSY	96	AVss
22	TEST1	47	IDED8	72	PIO5	97	V _{DD25}
23	TEST3	48	IDED7	73	CMB_STATE	98	VBUS
24	V _{DD33}	49	IDERSTB	74	V _{DD33}	99	SMC
25	V _{DD25}	50	Vss	75	V _{DD25}	100	Vss

Remark AVss(R) should be used to connect RREF through 1 % precision reference resistor of 2.43 k Ω .





1. PIN INFORMATION

(1/2)

Pin Name	I/O	Buffer Type	Active Level	Function
XIN	- 1	2.5 V Input		System clock input or oscillator In
XOUT	0	2.5 V Output		Oscillator out
RESETB	1	3.3 V Schmitt Input	Low	Asynchronous reset signaling
MD(1:0)	1	3.3 V Input		Function mode setting
IDECS(1:0)B	O (I/O)	5 V tolerant Output	Low	IDE host chip select
IDEA(2:0)	O (I/O)	5 V tolerant Output		IDE address bus
IDEINT	I (I/O)	5 V tolerant Input	High	IDE interrupt request from device to host
IDEDAKB	O (I/O)	5 V tolerant Output	Low	IDE DMA acknowledge
IDEIORDY	I (I/O)	5 V tolerant Input	High	IDE IO channel ready
IDEIORB	O (I/O)	5 V tolerant Output	Low	IDE IO read strobe
IDEIOWB	O (I/O)	5 V tolerant Output	Low	IDE IO write strobe
IDEDRQ	I (I/O)	5 V tolerant Input	High	IDE DMA request from device to host
IDED(15:0)	I/O	5 V tolerant I/O		IDE data bus
IDERSTB	O (I/O)	5 V tolerant Output	Low	IDE reset from host to device
DCC	I (I/O)	3.3 V Input		IDE controller operational mode setting
DV(1:0)	I (I/O)	3.3 V Input		Device select
CLC	I (I/O)	3.3 V Input		System clock setting
PWR	I (I/O)	3.3 V Input		Bus powered /self-powered select
CMB_BSY	O (I/O)	3.3 V Output		Combo IDE bus busy
CMB_STATE	I (I/O)	3.3 V Input		Combo IDE bus state
DPC	O (I/O)	3.3 V Output		Power control signaling for IDE device
SDA	I/O	3.3 V I/O		Serial ROM data signaling
SCL	I/O	3.3 V I/O		Serial ROM clock signaling
VBUS	1	5 V Schmitt Input Note		VBUS monitoring
DP	I/O	USB high speed D+ I/O		USB's high speed D+ signal
DM	I/O	USB high speed D- I/O		USB's high speed D- signal
RSDP	0	USB full speed D+ Output		USB's full speed D+ signal
RSDM	0	USB full speed D- Output		USB's full speed D- signal
RPU	Α	USB Pull-up control		1.5 kΩ pull-up resistor control
RREF	Α	Analog		Reference resistor
SPD	I (I/O)	3.3 V Input		NEC private
SMC	I	3.3 V Input		Scan mode control
TEST(3:0)	I	3.3 V Input		Test mode setting

Note VBUS pin may be used to monitor for VBUS line even if V_{DD33}, V_{DD25}, and AV_{DD25} are shut off. System must ensure that the input voltage level for VBUS pin is less than 3.0 V due to the absolute maximum rating is not exceeded.



(2/2)

Pin Name	I/O	Buffer Type	Active Level	Function
GPIO(7:0)	I/O	3.3 V Schmitt I/O		General purpose IO port (for future extension)
PIO(15:14)	I/O	3.3 V I/O		IO port (for future extension)
PIO(5)	I/O	3.3 V Schmitt I/O		IO port (for future extension)
IRQ0	I	3.3 V Schmitt Input	High	External interrupt input (for future extension)
AV _{DD25}				2.5 V V _{DD} for Analog circuit
V _{DD25}				2.5 V V _{DD}
V _{DD33}				3.3 V V _{DD}
AVss				Vss for Analog circuit
Vss				Vss

Remarks 1. "5 V tolerant" means that the buffer is 3.3 V buffer with 5 V tolerant circuit.

2. The signal marked as "(I/O)" in the above table operates as I/O signals during testing. However, they do not need to be considered in normal use.



2. FUNCTION INFORMATION

USB to IDE system can be realized by the μ PD720130, Serial ROM which has USB vender ID, product ID, etc, and power control circuit. The μ PD720130 can be selected bus powered mode or self powered mode. If all power consumption for USB to IDE system is less than the specification of bus powered device, it will be possible to realize high-speed capable bus powered system. The μ PD720130 has some features for bus powered system. Also, some system may control target IDE device by two IDE controllers. At the time, IDE bus arbitration should be required to each IDE controller. The μ PD720130 has a feature of IDE bus arbitration, too.

The setting of IDE controller in the μ PD720130 is controlled by data in serial ROM or external pin setting. If there is any inconsistency between data in serial ROM and external pin setting, the data in serial ROM is higher priority than external pin setting.

2.1 Data in Serial ROM

The μ PD720130 loads some data such as Vendor ID, Product ID and some additional USB related information, etc from serial ROM when the μ PD720130 is initialized. Example of data in serial ROM is as follows. ExPinReset and ExPinSet fields hold data which is related to the external pin setting.

Table 2-1. Data in Serial ROM

Data size	Symbol	Description
1 Word	Flags	Control for descriptor overwrite
1 Byte	ExPinReset	PWR, CLC, DCC, DV[1:0] Reset bit map field
1 Byte	ExPinSet	PWR, CLC, DCC, DV[1:0] Set bit map field
1 Word	idVendor	idVendor field in Device descriptor
1 Word	idProduct	idProduct field in Device descriptor
1 Word	bcdDevice	bcdDevice field in Device descriptor
1 Byte	MaxPower BUS	MaxPower field in Configuration descriptor for Bus powered mode
1 Byte	MaxPower Self	MaxPower field in Configuration descriptor for Self powered mode
1 Byte	bInterfaceClass	bInterfaceClass field in Interface descriptor
1 Byte	bInterfaceSubClass	bInterfaceSubClass field in Interface descriptor
1 Byte	bInterfaceProtocol	bInterfaceProtocol field in Interface descriptor
1 Word	TxMode Reset	IDE transmission type such as Ultra DMA 66 Reset bit map field
1 Word	TxMode Set	IDE transmission type such as Ultra DMA 66 Set bit map field
32 Bytes	ManufactureString	String descriptor for Manufacturer
32 Bytes	ProductString	String descriptor for Product
32 Bytes	SerialString	String descriptor for Device serial number



2.2 External Pin Setting

Usually, serial ROM should be used to keep Vendor ID, Product ID and some additional USB related information. And then, the external pin setting of the μ PD720130 is not so important to realize USB to IDE bridge system. The recommended external pin setting is as follows.

Table 2-2. Recommended External Pin Setting

Pin Name	Setting
MD1	1
MD0	0
SCL	Pull Up Note 1
SDA	Pull Up
DV1	"L" clamp
DV0	"L" clamp
CLC	"L" clamp
PWR	"L" clamp
DCC	Pull Down Note 2
GPIO(7:0)	"L" clamp
PIO(14:15)	"L" clamp
PIO5	"L" clamp
SPD	"H" clamp
TEST(3:0)	"L" clamp
SMC	"L" clamp
IRQ0	"L" clamp

Notes 1. If serial ROM size is more than 2 Kbytes, SCL should be pull down.

2. If target IDE device is not fixed, it is preferable that DCC pin can switch pull-up or pull-down.

The setting for any other pins such as CMB_BSY, CMB_STATE depends on USB2.0 to IDE Bridge system. For example, if two IDE controllers control one target IDE device and one of two IDE controllers is the μ PD720130, CMB_BSY and CMB_STATE are used to handshake between two IDE controller chips. On the other hand, when the μ PD720130 is only controller of target IDE device, CMB_BSY should be opened and CMB_STATE should be clamped to "L".





2.3 Control Bit in Serial ROM or External Pin Setting

The following tables show IDE status and control bit in serial ROM or external pin setting.

Table 2-3. DV1/DV0, CLC, PWR Setting

No.	Device Power	Internal	ATA/ATAPI	Setti	ing in Serial R	OM or Externa	ıl Pin															
		Clock		PWR	CLC	DV1	DV0															
0	Bus Powered	7.5 MHz	No device connected	1	1	1	1															
1			ATA	1	1	1	0															
2			ATAPI	1	1	0	1															
3			Reserved	1	1	0	0															
4		60 MHz	No device connected	1	0	1	1															
5			ATA	1	0	1	0															
6			ATAPI	1	0	0	1															
7			Reserved	1	0	0	0															
8	Self Powered	60 MHz	No device connected	0	1	1	1															
9			Combo (ATA)	0	1	1	0															
10			Combo (ATAPI)	0	1	0	1															
11			Reserved	0	1	0	0															
12			No device connected	0	0	1	1															
13										İ								ATA	0	0	1	0
14				ATAPI	0	0	0	1														
15			Auto device detect	0	0	0	0															

Remark Setting No. 0, 3, 4, 7, 8, 11, and 12 are prohibited to use.





Table 2-4. DV1/DV0, DCC Setting

	С	ondition		DCC	DCC Setting	Description	
DV1	DV0	Mode	Target Device	Pin Setting	in Serial ROM		
1	0	ATA	ATA	0	No setting	Ultra, Multi Word DMA are disabled	
				0	Reset	Ultra, Multi Word DMA are disabled	
				0	Set	Ultra, Multi Word DMA are enabled.	
				1	No setting	Ultra, Multi Word DMA are enabled.	
				1	Reset	Ultra, Multi Word DMA are disabled	
				1	Set	Ultra, Multi Word DMA are enabled.	
0	1	ATAPI	ATAPI	0	No setting	Ultra DMA is disabled	
				0	Reset	Ultra DMA is disabled	
				0	Set	Ultra, Multi Word DMA are enabled.	
				1	No setting	Ultra, Multi Word DMA are enabled.	
					1	Reset	Ultra DMA is disabled
				1	Set	Ultra, Multi Word DMA are enabled.	
0	0	Auto	ATA	0	No setting	Ultra, Multi Word DMA are disabled	
		device detect		0	Reset	Ultra, Multi Word DMA are disabled	
		detect		0	Set	Ultra, Multi Word DMA are enabled.	
				1	No setting	Ultra, Multi Word DMA are enabled.	
					1	Reset	Ultra, Multi Word DMA are disabled
				1	Set	Ultra, Multi Word DMA are enabled.	
			ATAPI	0	No setting	Ultra DMA is disabled	
				0	Reset	Ultra DMA is disabled	
				0	Set	Ultra, Multi Word DMA are enabled.	
				1	No setting	Ultra, Multi Word DMA are enabled.	
				1	Reset	Ultra DMA is disabled	
					1	Set	Ultra, Multi Word DMA are enabled.

Remark PIO mode 0-4 are always enabled.



2.4 Combo Mode Function

The μ PD720130 can be used to realize that two IDE controller chips control one target IDE device in one system. To realize IDE bus arbitration between two IDE controller chips, the μ PD720130 has CMB_BSY and CMB_STATE. Combo mode is enabled when PWR = 0 and CLC = 1.

CMB_BSY and CMB_STATE connect to other IDE controller chip as follows.

Figure 2-1. CMB_BSY and CMB_STATE Connection between Two IDE Controller Chips

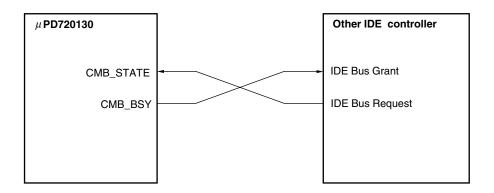


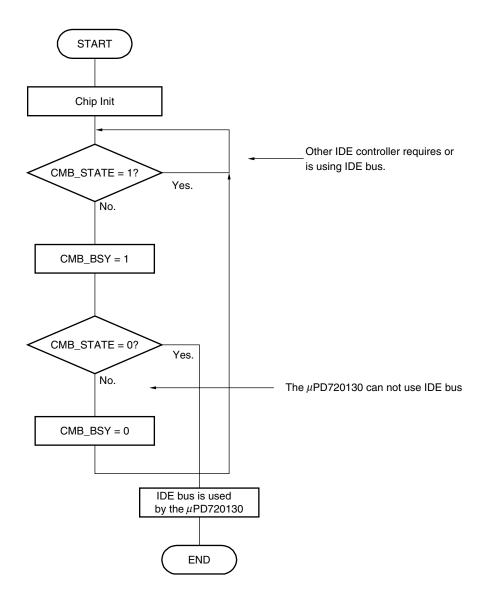
Table 2-5. Description of CMB_BSY and CMB_STATE

Pin Name	Direction	Value	Description
CMB_STATE	IN	0	Other IDE controller does not require or does not use IDE bus.
		1	Other IDE controller requires or is using IDE bus.
CMB_BSY	OUT	0	The μ PD720130 does not require or does not use IDE bus.
		1	The μ PD720130 requires or is using IDE bus.



The IDE bus arbitration will be done by following sequence. The μ PD720130 will confirm whether other IDE controller requires or is using IDE bus or not. If other IDE controller does not require or does not use IDE bus, the μ PD720130 will use IDE bus.

Figure 2-2. IDE Bus Arbitration Sequence

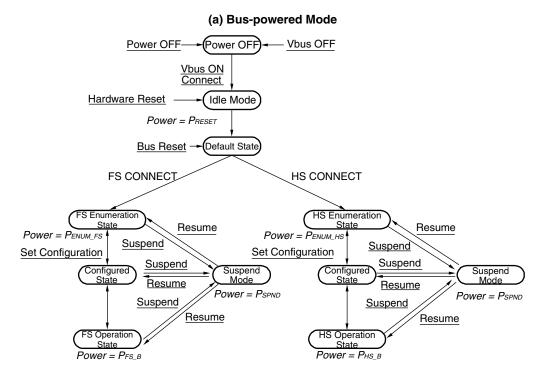




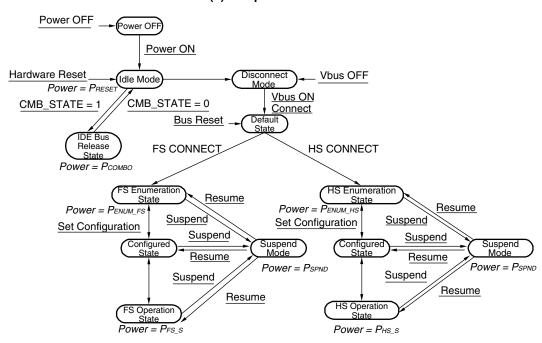
2.5 Power Control

To realize bus-powered or high performance self-powered USB2.0 to IDE Bridge system, the μ PD720130 has two internal system clock mode. One is 7.5 MHz for bus-powered mode and the other is 60 MHz for self-powered mode. The μ PD720130 controls the power state by events as follows. The word with under line shows event. The Italic word shows the power state.

Figure 2-3. Power State Control



(b) Self-powered Mode

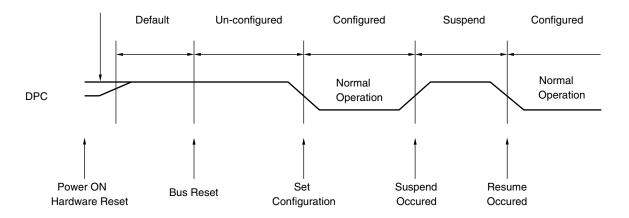




To realize bus-powered USB2.0 to IDE Bridge system, the power consumption for IDE device should be controlled by the power state of the μ PD720130. The μ PD720130 has DPC pin to control IDE device's power circuit. DPC pin's output level relates to USB device states. DPC should be pull up to 3.3 V because DPC output becomes high impedance state until the μ PD720130 is initialized.

Figure 2-4. DPC Pin to Control IDE Device's Power Circuit

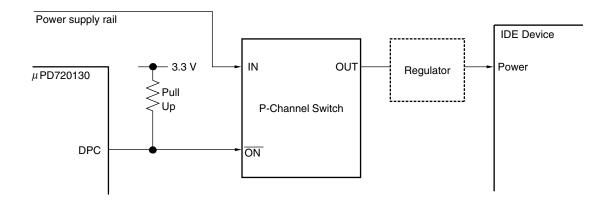
High impedance state



Following reference circuit can cut off power supply to IDE device during the μ PD720130 is under default and un-configured state. Also, the power supply to IDE device is disabled during suspend state, too.

Power consumption of total system under default, un-configured, and suspend state can be reduced by DPC pin.

Figure 2-5. Power Control Circuit Example





3. ELECTRICAL SPECIFICATIONS

3.1 Buffer List

• 2.5 V oscillator interface

XIN, XOUT

• 3.3 V input buffer

MD(1:0), TEST(3:0), SMC

• 3.3 V schmitt input buffer

RESETB, IRQ0

• 3.3 V input buffer with enable (OR type)

DCC, DV(1:0), SPD, CLC, PWR, CMB_STATE

• 3.3 V IoL = 6 mA 3-state output buffer

CMB_BSY, DPC

• 3.3 V IoL = 3 mA bi-directional schmitt buffer with input enable (OR-type)

GPIO(7:0), PIO5, SDA, SCL

• 3.3 V lo_L = 6 mA bi-directional buffer with input enable (OR-type)

PIO(15:14)

• 5 V schmitt input buffer

VBUS

• 5 V IoL = 6 mA 3-state output buffer

IDECS(1:0)B, IDEA(2:0), IDEDAKB, IDEIORB, IDEIOWB, IDERSTB

• 5 V IoL = 6 mA bi-directional buffer with input enable (OR-type)

IDED(15:0), IDEINT, IDEIORDY, IDEDRQ

USB interface

DP, DM, RSDP, RSDM, RREF, RPU

Remark Above, "5 V" refers to a 3.3 V buffer with 5-V tolerant circuit. Therefore, it is possible to have a 5-V connection for an external bus, but the output level will be only up to 3.3 V, which is the VDD33 voltage.





3.2 Terminology

Terms Used in Absolute Maximum Ratings

Parameter	Symbol	Meaning
Power supply voltage	VDD33, VDD25	Indicates voltage range within which damage or reduced reliability will not result when power is applied to a VDD pin.
Input voltage	Vı	Indicates voltage range within which damage or reduced reliability will not result when power is applied to an input pin.
Output voltage	Vo	Indicates voltage range within which damage or reduced reliability will not result when power is applied to an output pin.
Output current	lo	Indicates absolute tolerance value for DC current to prevent damage or reduced reliability when a current flows out of or into an output pin.
Operating temperature	Та	Indicates the ambient temperature range for normal logic operations.
Storage temperature	Tstg	Indicates the element temperature range within which damage or reduced reliability will not result while no voltage or current are applied to the device.

Terms Used in Recommended Operating Range

Parameter	Symbol	Meaning
Power supply voltage	V _{DD33} , V _{DD25}	Indicates the voltage range for normal logic operations occur when $V_{SS} = 0 \text{ V}$.
High-level input voltage	VIH	Indicates the voltage, which is applied to the input pins of the device, is the voltage indicates that the high level states for normal operation of the input buffer.
		* If a voltage that is equal to or greater than the "Min." value is applied, the input voltage is guaranteed as high level voltage.
Low-level input voltage	VIL	Indicates the voltage, which is applied to the input pins of the device, is the voltage indicates that the low level states for normal operation of the input buffer.
		* If a voltage that is equal to or lesser than the "Max." value is applied, the input voltage is guaranteed as low level voltage.
Hysteresys voltage	Vн	Indicates the differential between the positive trigger voltage and the negative trigger voltage.
Input rise time	tri	Indicates allowable input rise time to input pins. Input rise time is transition time from $0.1 \times V_{DD}$ to $0.9 \times V_{DD}$.
Input fall time	tri	Indicates allowable input fall time to input pins. Input fall time is transition time from $0.9 \times V_{DD}$ to $0.1 \times V_{DD}$.

Terms Used in DC Characteristics

Parameter	Symbol	Meaning
Off-state output leakage current	loz	Indicates the current that flows from the power supply pins when the rated power supply voltage is applied when a 3-state output has high impedance.
Output short circuit current	los	Indicates the current that flows when the output pin is shorted (to GND pins) when output is at high-level.
Input leakage current	lı	Indicates the current that flows when the input voltage is supplied to the input pin.
Low-level output current	loL	Indicates the current that flows to the output pins when the rated low-level output voltage is being applied.
High-level output current	Іон	Indicates the current that flows from the output pins when the rated high-level output voltage is being applied.



3.3 Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Power supply voltage	V _{DD33}	3.3 V power supply rail	-0.5 to +4.6	V
	V _{DD25}	2.5 V power supply rail	-0.5 to +3.6	V
Input voltage, 5 V buffer	Vı	$3.0 \text{ V} \le \text{V}_{\text{DD33}} \le 3.6 \text{ V}$ V _I < V _{DD33} + 3.0 V	-0.5 to +6.6	٧
Input voltage, 3.3 V buffer	Vı	$3.0 \text{ V} \le \text{V}_{\text{DD33}} \le 3.6 \text{ V}$ V _I < V _{DD33} + 1.0 V	-0.5 to +4.6	V
Input voltage, 2.5 V buffer	Vı	$2.3 \text{ V} \le \text{V}_{\text{DD25}} \le 2.7 \text{ V}$ V _I < V _{DD25} + 0.9 V	-0.5 to +3.6	V
Output voltage, 5 V buffer	Vo	3.0 V ≤ V _{DD33} ≤ 3.6 V Vo < V _{DD33} + 3.0 V	-0.5 to +6.6	V
Output voltage, 3.3 V buffer	Vo	3.0 V ≤ V _{DD33} ≤ 3.6 V Vo < V _{DD33} + 1.0 V	-0.5 to +4.6	V
Output voltage, 2.5 V buffer	Vo	$2.3 \text{ V} \le \text{V}_{\text{DD25}} \le 2.7 \text{ V}$ Vo < VDD25 + 0.9 V	-0.5 to +3.6	V
Output current, 5 V buffer	lo	IoL = 6 mA	20	mA
Output current, 3.3 V buffer	lo	IoL = 6 mA	20	mA
		IoL = 3 mA	10	mA
Operating ambient temperature	TA		0 to +70	°C
Storage temperature	T _{stg}		−65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameters. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

The ratings and conditions indicated for DC characteristics and AC characteristics represent the quality assurance range during normal operation.

Two Power Supply Rails Limitation

The μ PD720130 has two power supply rails (2.5 V, 3.3 V). The system will require the time when power supply rail is stable at V_{DD} level. And, there will be difference between the time of V_{DD25} and V_{DD33}. The μ PD720130 requires that V_{DD25} should be stable before V_{DD33} becomes stable. At this case, the system must ensure that the absolute maximum ratings for V_I / Vo are not exceeded. System reset signaling should be asserted more than specified time after both V_{DD25} and V_{DD33} are stable.





Recommended Operating Ranges

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Operating voltage	V _{DD33}	3.3 V for V _{DD33} pins	3.0	3.3	3.6	V
	V _{DD25}	2.5 V for V _{DD25} pins	2.3	2.5	2.7	V
	V _{DD25}	2.5 V for AV _{DD25} pins	2.3	2.5	2.7	V
High-level input voltage	VIH					
5.0 V high-level input voltage			2.0		5.5	V
3.3 V high-level input voltage			2.0		V _{DD33}	V
2.5 V high-level input voltage			1.7		V _{DD25}	V
Low-level input voltage	VIL					
5.0 V low-level input voltage			0		0.8	V
3.3 V low-level input voltage			0		0.8	V
2.5 V low-level input voltage			0		0.7	V
Hysteresis voltage	VH					
5 V hysteresis voltage			0.3		1.5	V
3.3 V hysteresis voltage			0.2		1.0	V
Input rise time	tri					
Normal buffer			0		200	ns
Schmitt buffer			0		10	ms
Input fall time	tfi					
Normal buffer			0		200	ns
Schmitt buffer			0		10	ms





DC Characteristics (VDD33 = 3.0 to 3.6 V, VDD25 = 2.3 to 2.7 V, TA = 0 to +70°C)

Control Pin Block

Parameter	Symbol	Condition	Min.	Max.	Unit
Off-state output current	loz	Vo = VDD33, VDD25 Or VSS		±10	μΑ
Output short circuit current	los Note			-250	mA
Low-level output current	loL				
5.0 V low-level output current		Vol = 0.4 V	6.0		mA
3.3 V low-level output current		Vol = 0.4 V	6.0		mA
3.3 V low-level output current		Vol = 0.4 V	3.0		mA
High-level output current	Іон				
5.0 V high-level output current		Vон = 2.4 V	-2.0		mA
3.3 V high-level output current		Vон = 2.4 V	-6.0		mA
3.3 V high-level output current		Vон = 2.4 V	-3.0		mA
Input leakage current	lı				
3.3 V buffer		VI = VDD or Vss		±10	μΑ
5.0 V buffer		VI = VDD or Vss		±10	μΑ

Note The output short circuit time is one second or less and is only for one pin on the LSI.





USB Interface Block

Parameter	Symbol	Conditions	Min.	Max.	Unit
Serial Resistor between DP (DM) and RSDP (RSDM)	Rs		38.61	39.39	Ω
Output pin impedance	ZHSDRV	Includes Rs resistor	40.5	49.5	Ω
Bus pull-up resistor on upstream facing port	Rpu	1.5 k Ω ±5% consists of resistance of transistor and pull-up resistor	1.485	1.515	Ω
Termination voltage for upstream facing port pull-up	VTERM		3.0	3.6	V
Input Levels for Full-speed:					
High-level input voltage (drive)	VIH		2.0		V
High-level input voltage (floating)	VIHZ		2.7	3.6	
Low-level input voltage	VIL			0.8	V
Differential input sensitivity	V _{DI}	(D+) – (D–)	0.2		V
Differential common mode range	Vсм	Includes Vol range	0.8	2.5	V
Output Levels for Full-speed:					
High-level output voltage	Vон	R _L of 14.25 kΩ to Vss	2.8	3.6	V
Low-level output voltage	Vol	R∟ of 1.425 kΩ to 3.6 V	0.0	0.3	V
SE1	Vose1		0.8		V
Output signal crossover point voltage	Vcrs		1.3	2.0	V
Input Levels for High-speed:					
High-speed squelch detection threshold (differential signal)	VHSSQ		100	150	mV
High-speed disconnect detection threshold (differential signal)	VHSDSC		525	625	mV
High-speed data signaling common mode voltage range	VHSCM		-50	+500	mV
High-speed differential input signaling level	See Figure	3-4.	•	•	•
Output Levels for High-speed:	•				
High-speed idle state	VHSOI		-10.0	+10.0	mV
High-speed data signaling high	Vнsон		360	440	mV
High-speed data signaling low	VHSOL		-10.0	+10.0	mV
Chirp J level (differential signal)	VCHIRPJ		700	1100	mV
Chirp K level (differential signal)	VCHIRPK		-900	-500	mV

Figure 3-1. Differential Input Sensitivity Range for Low-/full-speed

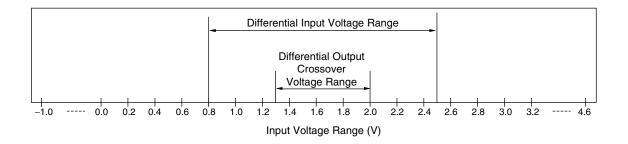


Figure 3-2. Full-speed Buffer Von/Ion Characteristics for High-speed Capable Transceiver

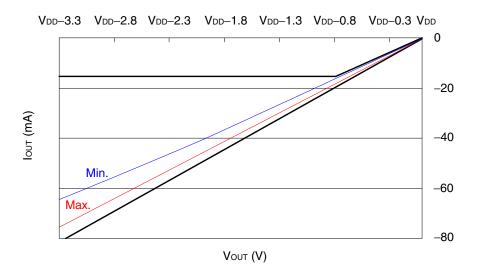


Figure 3-3. Full-speed Buffer Vol/IoL Characteristics for High-speed Capable Transceiver

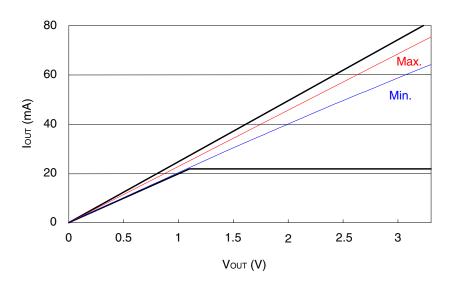


Figure 3-4. Receiver Sensitivity for Transceiver at DP/DM

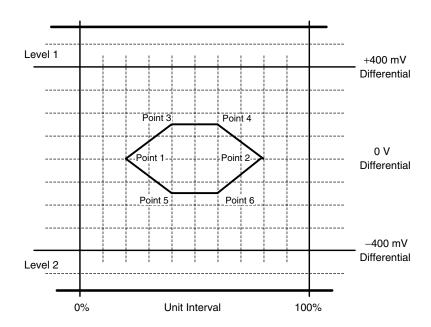
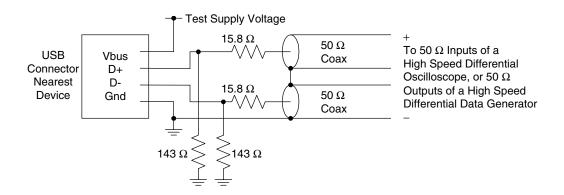


Figure 3-5. Receiver Measurement Fixtures



Pin Capacitance

Parameter	Symbol	Condition	Min.	Max.	Unit
Input capacitance	CIN	V _{DD} = 0 V, T _A = 25°C	4	6	pF
Output capacitance	Соит	fc = 1 MHz	4	6	pF
I/O capacitance	Сю	Unmeasured pins returned to 0 V	4	6	pF



Power Consumption

(1) The power consumption when device works as bus-powered mode

Symbol	Condition	Max.		Unit	
		V _{DD25}	V _{DD33}	AV _{DD25}	
PENUM-BUS	The power consumption under unconfigured stage				
	High-speed operating	57	3	10	mA
	Full-speed operating	23	4	10	mA
Pw-BUS	The power consumption when device works				
	High-speed operating	110	22	10	mA
	Full-speed operating	113	13	10	mA
Pw_spd-bus	The power consumption under suspend state	10	235	5	μΑ

(2) The power consumption when device works as self-powered mode

Symbol	Condition		Max.		Unit
		V _{DD25}	V_{DD33}	AV _{DD25}	
PENUM-SELF	The power consumption under unconfigured stage				
	High-speed operating Full-speed operating	85 60	5 5	10 10	mA mA
Pw-self	The power consumption when device works				
	High-speed operating Full-speed operating	120 113	25 13	10 10	mA mA
Pw_spd-self	The power consumption under suspend state	50	5	5	mA
Pw_unp	The power consumption under unplug state	87	3	10	mA
Рw_сом	The power consumption under combo mode	90	5	10	mA
	The device is releasing the IDE bus.				





AC Characteristics (VDD33 = 3.0 to 3.6 V, VDD25 = 2.3 to 2.7 V, TA = 0 to +70°C)

System Clock Ratings

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Clock frequency	fclk	X'tal	-500	30	+500	MHz
			ppm		ppm	
		Oscillator block	-500	30	+500	MHz
			ppm		ppm	
Clock duty cycle	t DUTY		45	50	55	%

Remarks 1. Recommended accuracy of clock frequency is \pm 100 ppm.

2. Required accuracy of X'tal or Oscillator block is including initial frequency accuracy, the spread of X'tal capacitor loading, supply voltage, temperature, and aging, etc.

System Reset signaling

Parameter	Symbol	Conditions	Min.	Max.	Unit
Reset active time	trst		2		μs

USB Interface Block

(1/2)

Parameter	Symbol	Conditions	Min.	Max.	Unit
Full-speed Source Electrical Characteristic	cs				
Rise time (10% - 90%)	tfR	$C_L = 50 \text{ pF},$ $R_S = 36 \Omega$	4	20	ns
Fall time (90% - 10%)	tff	$C_L = 50 \text{ pF},$ $R_S = 36 \Omega$	4	20	ns
Differential rise and fall time matching	t FRFM	(tfr/tff)	90	111.11	%
Full-speed data rate for device which are high-speed capable	t fdraths	Average bit rate	11.9940	12.0060	Mbps
Frame interval	t FRAME		0.9995	1.0005	ms
Consecutive frame interval jitter	trfi	No clock adjustment		42	ns
Source jitter total (including frequency tolerance):					
To next transition For paired transitions	tous		-3.5 -4.0	+3.5 +4.0	ns ns
Source jitter for differential transition to SE0 transition	t FDEOP		-2	+5	ns
Receiver jitter: To next transition For paired transitions	tura tura		–18.5 –9	+18.5 +9	ns ns
Source SE0 interval of EOP	t FEOPT		160	175	ns
Receiver SE0 interval of EOP	t FEOPR		82		ns
Width of SE0 interval during differential transition	tғsт			14	ns





(2/2)

					(2/2
Parameter	Symbol	Conditions	Min.	Max.	Unit
High-speed Source Electrical Characterist	ics				
Rise time (10% - 90%)	thsr		500		ps
Fall time (90% - 10%)	thsf		500		ps
Driver waveform	See Figure	3-6 .	•	•	
High-speed data rate	thsdrat		479.760	480.240	Mbps
Microframe interval	thsfram		124.9375	125.0625	μs
Consecutive microframe interval difference	thsrFi			4 high-speed	Bit times
Data source jitter	See Figure	3-6 .			
Receiver jitter tolerance	See Figure	e 3-4.			
Device Event Timings					
Time from internal power good to device pulling D+ beyond V _{IHZ} (min.) (signaling attached)	tsigatt			100	ms
Debounce interval provided by USB system software after attach	tattdb			100	ms
Inter-packet delay for full-speed	tipo		2		Bit times
Inter-packet delay for device response w/detachable cable for full-speed	trspipd1			6.5	Bit times
High-speed detection start time from suspend	tsca		2.5		μs
Sample time for suspend vs reset	tcsr		100	875	μs
Time to detect bus suspend state	tspd		3.000	3.125	ms
Power down under suspend	tsus			10	ms
Reversion time from suspend to high-speed	tпнs			1.333	μs
Drive Chirp K width	tско		1		ms
Finish Chirp K assertion	trca			7	ms
Start sequencing Chirp K-J-K-J-K-J	tssc			100	μs
Finish sequencing Chirp K-J	trsc		-500	-100	μs
Detect sequencing Chirp K-J width	tcsı		2.5		μs
Sample time for sequencing Chirp	tscs		1	2.5	ms
Reversion time to high-speed	t rha			500	μs
High-speed detection start time	thos		2.5	3000	μs
Reset completed time	tors		10		ms
	•				



IDE Interface Block

PIO mode

Parameter	Symbol	Mode 0	Mode 1	Mode 2	Mode 3	Mode 4	Unit
Cycle time (min.)	to	600	383	240	180	120	ns
Address setup time (min.)	t ₁	70	50	30	30	25	ns
16 bits DIOR/DIOW pulse width (min.)	t ₂	165	125	100	80	70	ns
8 bits DIOR/DIOW pulse width (min.)		290	290	290	80	70	ns
DIOR/DIOW recovery time (min.)	t _{2i}	_	_	_	70	25	ns
DIOW data setup time (min.)	tз	60	45	30	30	20	ns
DIOW data hold time (min.)	t ₄	30	20	15	10	10	ns
DIOR data setup time (min.)	t 5	50	35	20	20	20	ns
DIOR data hold time (min.)	t ₆	5	5	5	5	5	ns
DIOR 3-state delay time (max.)	t ₆ z	30	30	30	30	30	ns
Address hold time (min.)	t ₉	20	15	10	10	10	ns
IORDY read data valid time (min.) Note	tro	0	0	0	0	0	ns
IORDY setup time (min.) Note	tA	35	35	35	35	35	ns
IORDY pulse width (max.) Note	tв	1250	1250	1250	1250	1250	ns
IORDY Inactive to Hi-Z time (max.) Note	tc	5	5	5	5	5	ns

Note IORDY is an option in mode 0 - 2. IORDY is essential in modes 3 and 4.

Multi Word DMA mode

Parameter	Symbol	Mode 0	Mode 1	Mode 2	Unit
Cycle time (min.)	to	480	150	120	ns
DIOR/DIOW pulse width (min.)	to	215	80	70	ns
DIOR data access time (max.)	t⊨	150	60	50	ns
DIOR data hold time (min.)	tF	5	5	5	ns
DIOR data setup time (min.)	t Gr	100	30	20	ns
DIOW data setup time (min.)	t _{Gw}	100	30	20	ns
DIOW data hold time (min.)	tн	20	15	10	ns
DMACK setup time (min.)	tı	0	0	0	ns
DMACK hold time (min.)	t∍	20	5	5	ns
DIOR negate pulse width (min.)	tĸr	50	50	25	ns
DIOW negate pulse width (min.)	tĸw	215	50	25	ns
DIOR-DMARQ delay time (max.)	t∟r	120	40	35	ns
DIOW-DMARQ delay time (max.)	tLw	40	40	35	ns
DMACK 3-state delay time (max.)	tz	20	25	25	ns
CS setup time (min.)	tм	50	30	25	ns
CS hold time (min.)	tn	15	10	10	ns





Ultra DMA mode

Parameter	Symbol	Мо	de 0	Мос	de 1	Мо	de 2	Мос	de 3	Мо	de 4	Unit
		Min.	Max.									
Average cycle time for 2 cycles	t2CYC	240	-	160	-	120	-	90	-	60	-	ns
Minimum cycle time for 2 cycles	t2CYC	235	-	156	-	117	-	86	-	57	-	ns
Cycle time for 1 cycle	toyo	114	-	75	-	55	-	39	-	25	-	ns
Data setup time on receive side	tos	15	-	10	-	7	-	7	-	5	-	ns
Data hold time on receive side	tон	5	-	5	-	5	-	5	-	5	-	ns
Data setup time on transmit side	tovs	70	-	48	-	34	-	20	-	6	-	ns
Data hold time on transmit side	tоvн	6	-	6	-	6	-	6	-	6	-	ns
First STROBE time	trs	0	230	0	200	0	170	0	130	0	120	ns
Interlock time with limitation	t⊔	0	150	0	150	0	150	0	100	0	100	ns
Minimum interlock time	tmLi	20	-	20	-	20	-	20	-	20	-	ns
Interlock time without limitation	tui	0	-	0	-	0	-	0	-	0	-	ns
Output release time	taz	-	10	-	10	-	10	-	10	-	10	ns
Output delay time	t zah	20	-	20	-	20	-	20	-	20	-	ns
Output stabilization time (from release)	t zad	0	-	0	-	0	-	0	-	0	-	ns
Envelope time	tenv	20	70	20	70	20	70	20	55	20	55	ns
STROBE DMARDY delay time	tsr	-	50	1	30	-	20	1	NA	-	NA	ns
Last STROBE time	trfs	-	75	1	60	-	50	1	60	-	60	ns
Pause time	t _{RP}	160	-	125	-	100	-	100	-	100	-	ns
IORDY pull-up time	tioryz	-	20	-	20	-	20	-	20	-	20	ns
IORDY wait time	tziory	0	-	0	-	0	-	0	-	0	-	ns
DMACK setup/hold time	tack	20	-	20	-	20	-	20	-	20	-	ns
STROBE STOP time	tss	50	-	50	-	50	-	50	-	50	-	ns





Serial ROM interface Block

Parameter	Symbol	Conditions	Min.	Max.	Unit
Clock frequency	tscL			100	KHz
Clock pulse width low	tLOW		4.7		μs
Clock pulse width high	tніgн		4.0		μs
Clock Low to data valid	taa		100	4500	ns
Start hold time	thd.sta		4.0		μs
Start setup time	tsu.sta		4.7		μs
Data in hold time	thd.dat		0		ns
Data in setup time	tsu.dat		0.2		μs
Data out hold time	tон		50		ns
Stop setup time	tsu.sto		4.7		μs
Time the bus must be free before a new transmission can start	t BUF		10		μs
Write cycle time	twn		10		ms

Figure 3-6. Transmit Waveform for Transceiver at DP/DM

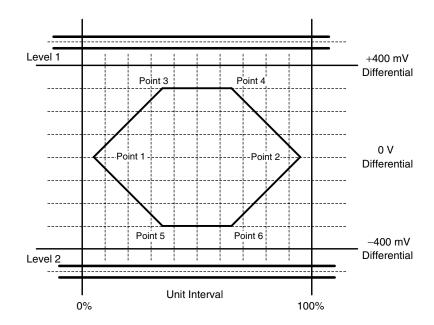
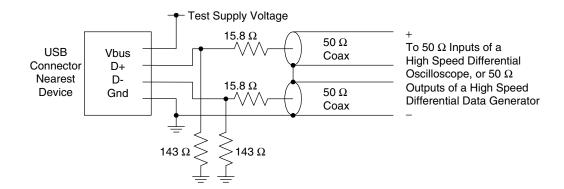


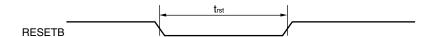
Figure 3-7. Transmitter Measurement Fixtures





Timing Diagram

System reset timing

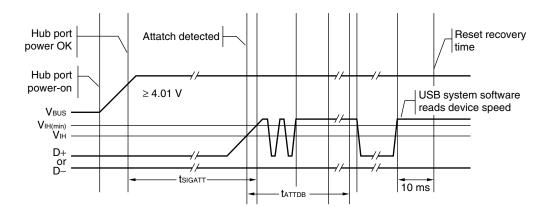


Remark After RESET is negated, this chip read the serial ROM first. Do not reset while the serial ROM is read. The serial ROM is completed to read below time, after RESET is negated.

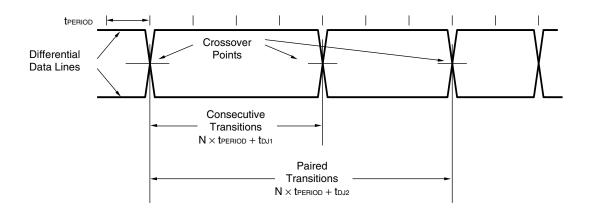
5 + 0.1197 × bytes (serial ROM size) + 0.5678 (ms)

Example In the case of 512 bytes: 66.855 ms, in the case of 8 Kbytes: 986.15 ms

USB power-on and connection events

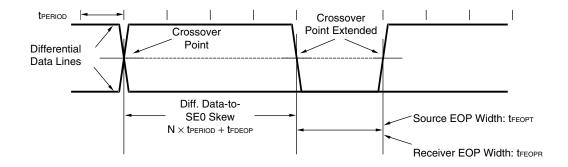


USB differential data jitter for full-speed

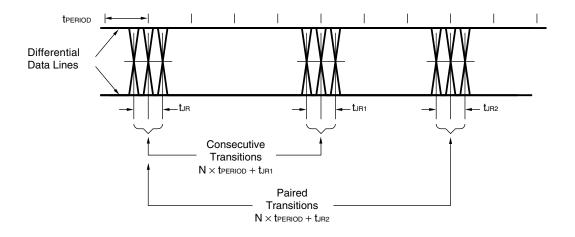




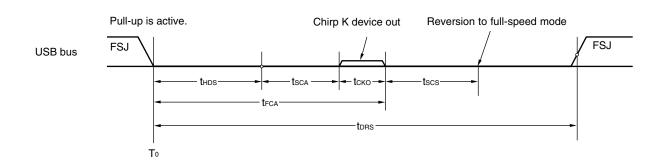
USB differential-to-EOP transition skew and EOP width for full-speed



USB receiver jitter tolerance for full-speed



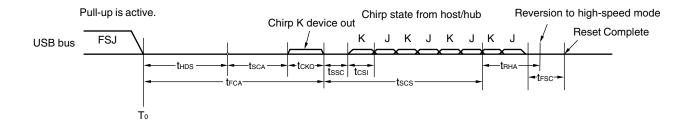
USB connection sequence on full-speed system bus



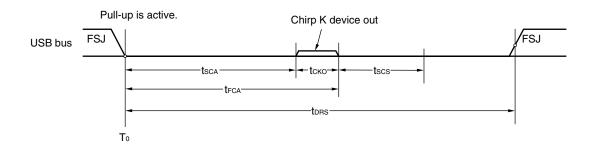




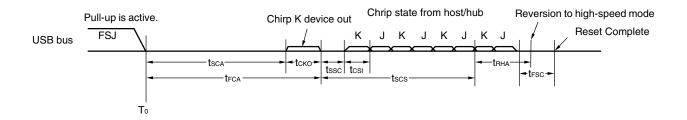
USB connection sequence on high-speed system bus



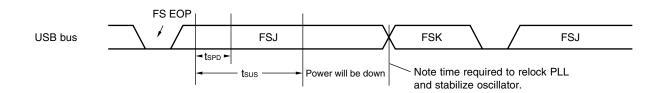
USB reset sequence from suspend state on full-speed system bus



USB reset sequence from suspend state on high-speed system bus

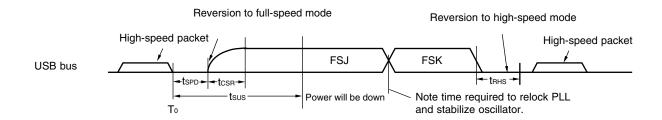


USB suspend and resume on full-speed system bus

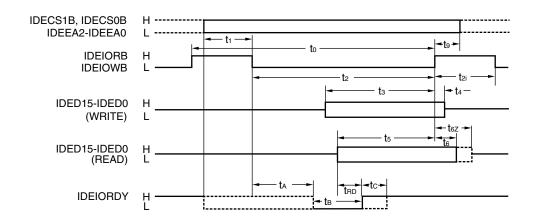




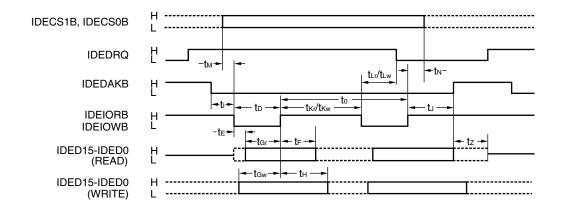
USB suspend and resume on high-speed system bus



IDE PIO mode timing

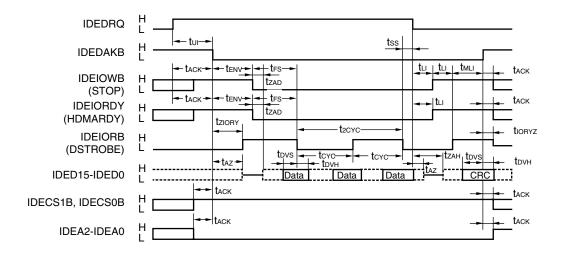


IDE multi word DMA mode timing

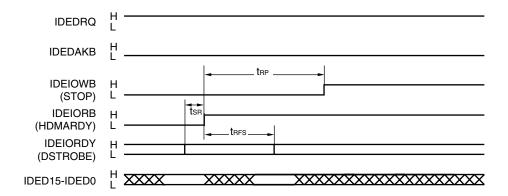




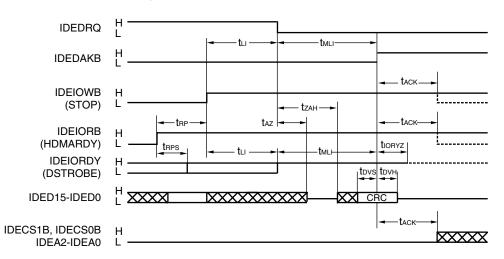
IDE ultra DMA mode data-in timing



IDE ultra DMA mode data-in stop timing

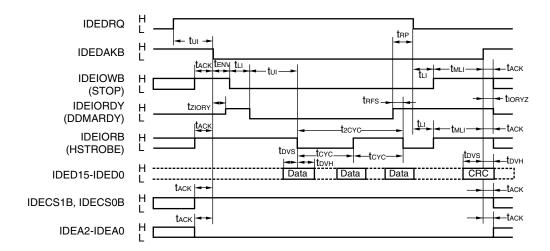


IDE ultra DMA mode data-in end timing

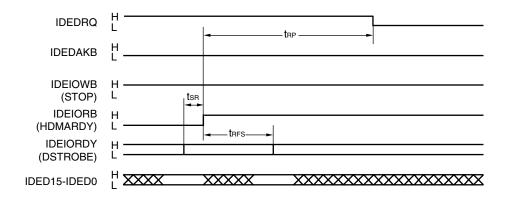


IDE ultra DMA mode data-out timing

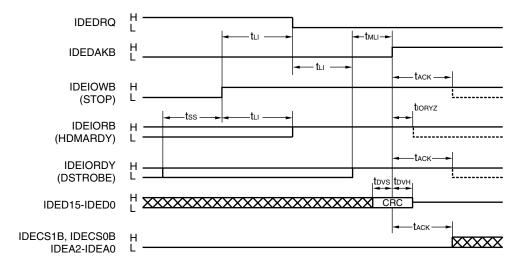




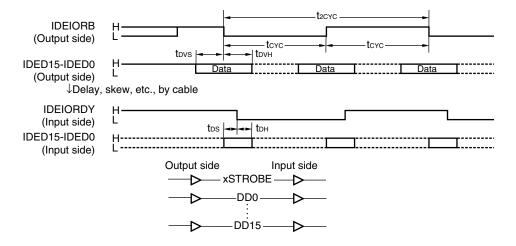
IDE ultra DMA mode data-out stop timing



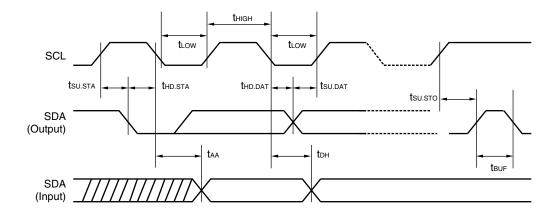
IDE ultra DMA mode data-out end timing



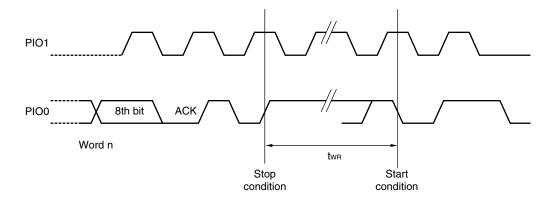
IDE ultra DMA mode data skew timing



Serial ROM access timing



Serial ROM write cycle timing

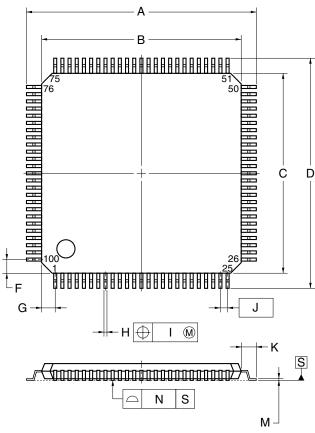




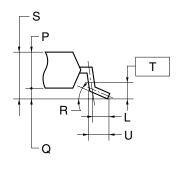
4. PACKAGE DRAWING

- μPD720130GC-9EU
- μPD720130GC-9EU-A

100-PIN PLASTIC TQFP (FINE PITCH) (14x14)



detail of lead end



NOTE

Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.

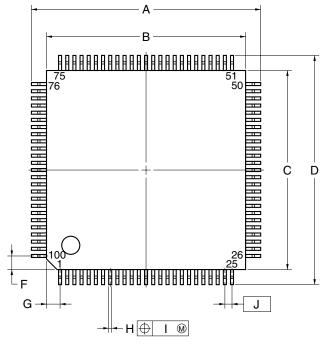
ITEM	MILLIMETERS
Α	16.0±0.2
В	14.0±0.2
С	14.0±0.2
D	16.0±0.2
F	1.0
G	1.0
Н	0.22±0.05
I	0.08
J	0.5 (T.P.)
K	1.0±0.2
L	0.5
М	$0.17^{+0.03}_{-0.07}$
N	0.08
Р	1.0
Q	0.1±0.05
R	3°+4°
S	1.1±0.1
Т	0.25
U	0.6±0.15
	P100GC-50-9EU

P100GC-50-9EU

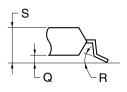


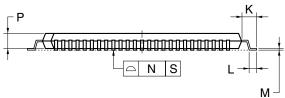
• μPD720130GC-9EU-SIN

100-PIN PLASTIC TQFP (FINE PITCH) (14x14)



detail of lead end





NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	16.0±0.2
В	14.0±0.2
С	14.0±0.2
D	16.0±0.2
F	1.0
G	1.0
Н	$0.22^{+0.05}_{-0.04}$
ı	0.10
J	0.5 (T.P.)
K	1.0±0.2
L	0.5±0.2
М	$0.145^{+0.055}_{-0.045}$
N	0.10
Р	1.0±0.1
Q	0.1±0.05
R	3°+7° -3°
S	1.27 MAX.
	040000 50 0511

S100GC-50-9EU-2





5. RECOMMENDED SOLDERING CONDITIONS

The μ PD720130 should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, contact your NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Recommended Soldering Conditions of Surface-Mount Type

 μ PD720130GC-9EU: 100-pin plastic TQFP (Fine pitch) (14 × 14)

 μ PD720130GC-9EU-SIN: 100-pin plastic TQFP (Fine pitch) (14 × 14)

Soldering Method	Soldering Conditions	Symbol
Infrared ray reflow	Peak package's surface temperature :235° C, Reflow time: 30 seconds or less (210 °C or higher), Maximum allowable number of reflow processes: 2, Exposure limit Note: 3 days (10 hours pre-backing is required at 125C° afterwards). <caution> Non-heat-resistant trays, such as magazine and taping trays, cannot be baked before unpacking.</caution>	IR35-103-2
Partial heating method	Pin temperature: 300°C or below, Heat time: 3 seconds or less (per each side of the device).	-

Note The Maximum number of days during which the product can be stored at a temperature of 25°C and a relative humidity of 65% or less after dry-pack package is opened.

★ μ PD720130GC-9EU-A: 100-pin plastic TQFP (Fine pitch) (14 × 14)

Soldering Method	Soldering Conditions	Symbol
Infrared ray reflow	Peak package's surface temperature :235° C, Reflow time: 30 seconds or less (210 °C or higher), Maximum allowable number of reflow processes: 2, Exposure limit Note: 3 days (10 hours pre-backing is required at 125C° afterwards), Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended. <caution> Non-heat-resistant trays, such as magazine and taping trays, cannot be baked before unpacking.</caution>	IR35-103-2
Partial heating method	Pin temperature: 300°C or below,	-
	Heat time: 3 seconds or less (per each side of the device).	

Note The Maximum number of days during which the product can be stored at a temperature of 25°C and a relative humidity of 65% or less after dry-pack package is opened.

[MEMO]

[MEMO]

[MEMO]



NOTES FOR CMOS DEVICES -

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

5 POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.



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